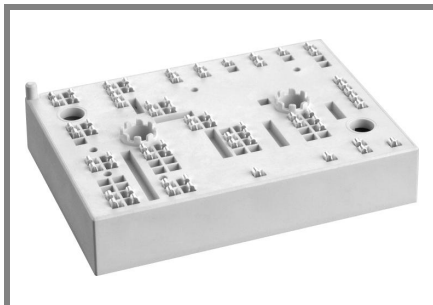


SKiiP 39AC065V2



MiniSKiiP® 3

3-phase bridge inverter

SKiiP 39AC065V2

Features

- Ultrafast NPT IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications

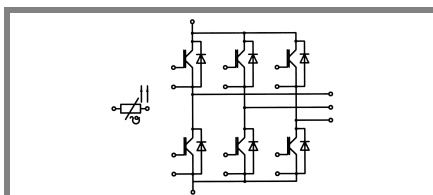
- Inverter up to 30 kVA
- Typical motor power 15 kW

Remarks

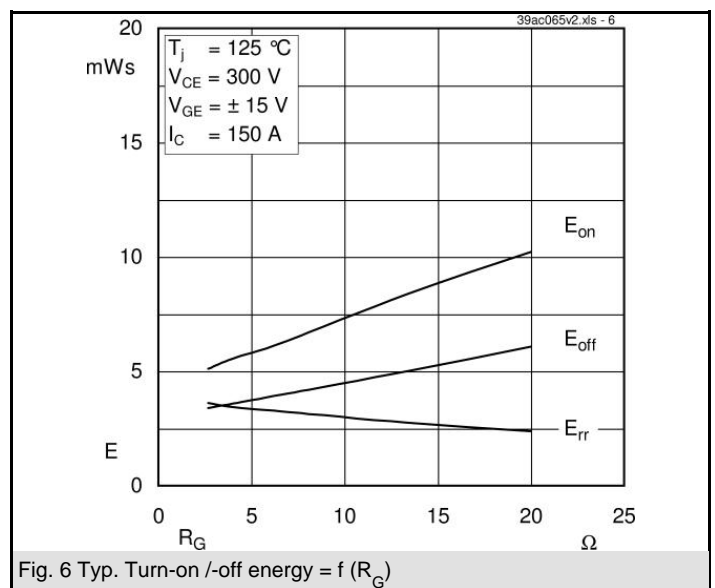
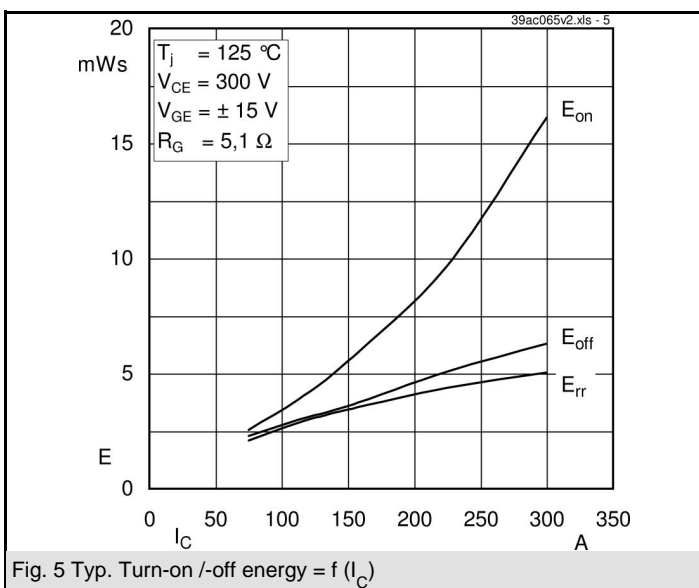
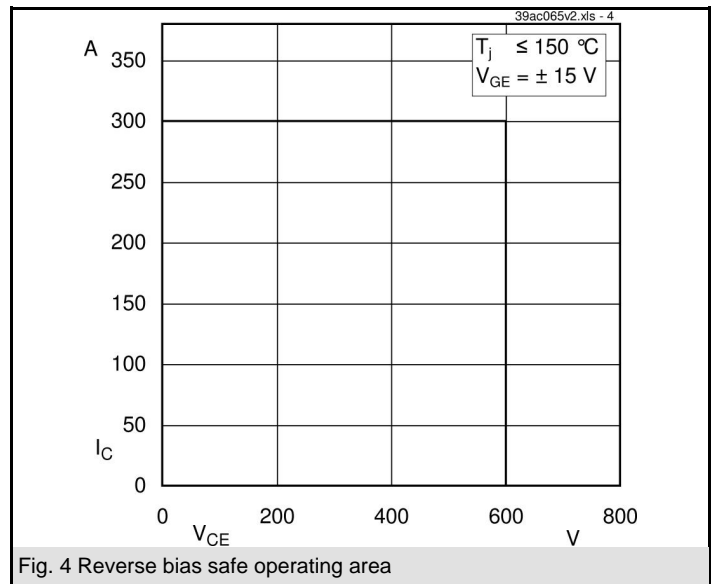
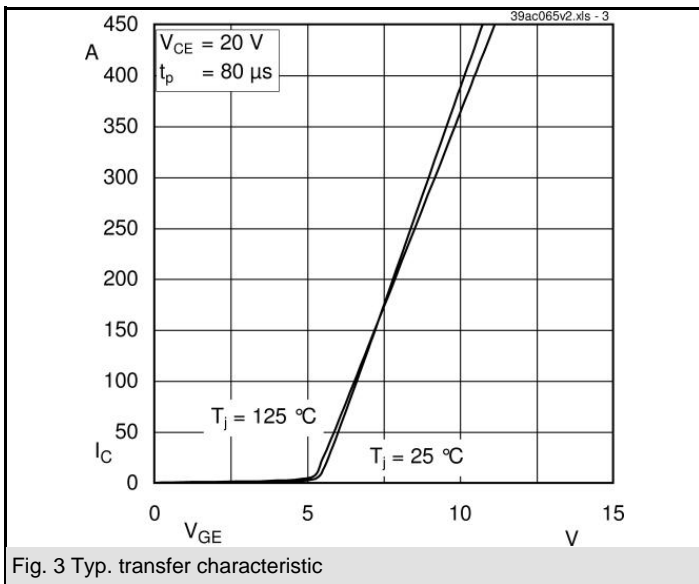
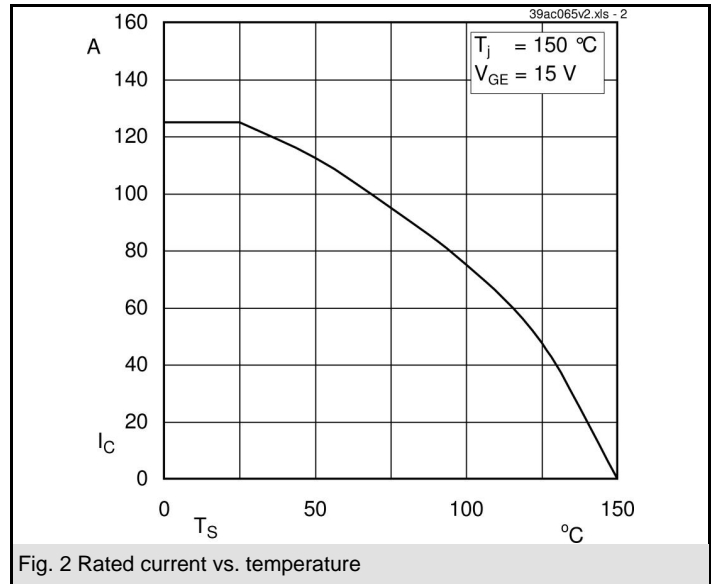
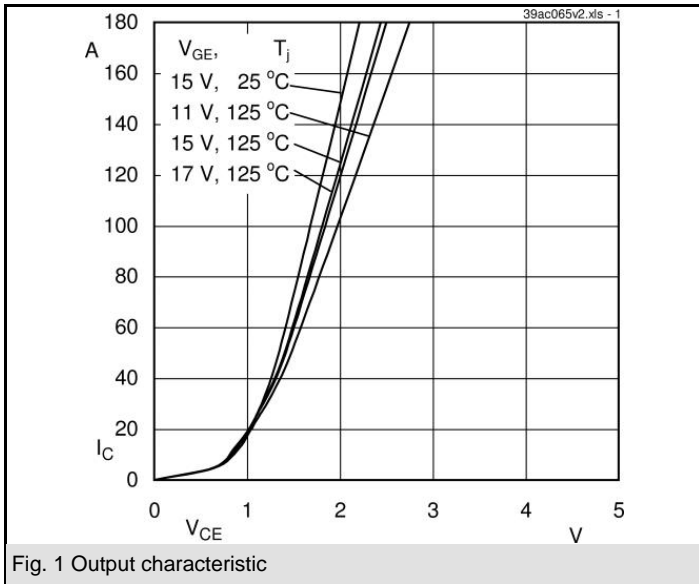
- V_{CEsat} , V_F = chip level value

Absolute Maximum Ratings		$T_s = 25\text{ °C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT - Inverter			
V_{CES}	$T_s = 25\text{ (70) °C}$ $t_p \leq 1\text{ ms}$	600	V
I_C		125 (93)	A
I_{CRM}		300	A
V_{GES}		± 15	V
T_j		- 40 ... + 150	°C
Diode - Inverter			
I_F	$T_s = 25\text{ (70) °C}$ $t_p \leq 1\text{ ms}$	120 (89)	A
I_{FRM}		300	A
T_j		- 40 ... + 150	°C
I_{tRMS}	per power terminal (20 A / spring)	160	A
T_{stg}	$T_{op} \leq T_{stg}$	- 40 ... + 125	°C
V_{isol}	AC, 1 min.	2500	V

Characteristics		$T_s = 25\text{ °C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT - Inverter					
V_{CEsat}	$I_{Cnom} = 150\text{ A}$, $T_j = 25\text{ (125) °C}$		2 (2,2)	2,5 (2,7)	V
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 3\text{ mA}$	3	4	5	V
$V_{CE(TO)}$	$T_j = 25\text{ (125) °C}$		1,2 (1,1)	1,3 (1,2)	V
r_T	$T_j = 25\text{ (125) °C}$		5,3 (7,3)	8 (10)	mΩ
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		9		nF
C_{oes}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		1,7		nF
C_{res}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		2,1		nF
$R_{th(j-s)}$	per IGBT		0,4		K/W
$t_{d(on)}$	under following conditions		20		ns
t_r	$V_{CC} = 300\text{ V}$, $V_{GE} = \pm 15\text{ V}$		25		ns
$t_{d(off)}$	$I_{Cnom} = 150\text{ A}$, $T_j = 125\text{ °C}$		185		ns
t_f	$R_{Gon} = R_{Goff} = 5,1\text{ Ω}$		15		ns
E_{on}	inductive load		6,4		mJ
E_{off}			3,7		mJ
Diode - Inverter					
$V_F = V_{EC}$	$I_{Fnom} = 150\text{ A}$, $T_j = 25\text{ (125) °C}$		1,7 (1,7)	2,1 (2,1)	V
$V_{(TO)}$	$T_j = 25\text{ (125) °C}$		1 (0,9)	1,1 (1)	V
r_T	$T_j = 25\text{ (125) °C}$		4,7 (5,3)	6,7 (7,3)	mΩ
$R_{th(j-s)}$	per diode		0,55		K/W
I_{RRM}	under following conditions		270		A
Q_{rr}	$I_{Fnom} = 150\text{ A}$, $V_R = 300\text{ V}$		18		μC
E_{rr}	$V_{GE} = 0\text{ V}$, $T_j = 125\text{ °C}$ $di_F/dt = 13700\text{ A/μs}$		3,5		mJ
Temperature Sensor					
R_{ts}	3 %, $T_r = 25\text{ (100) °C}$		1000(1670)		Ω
Mechanical Data					
m			95		g
M_s	Mounting torque	2		2,5	Nm



AC



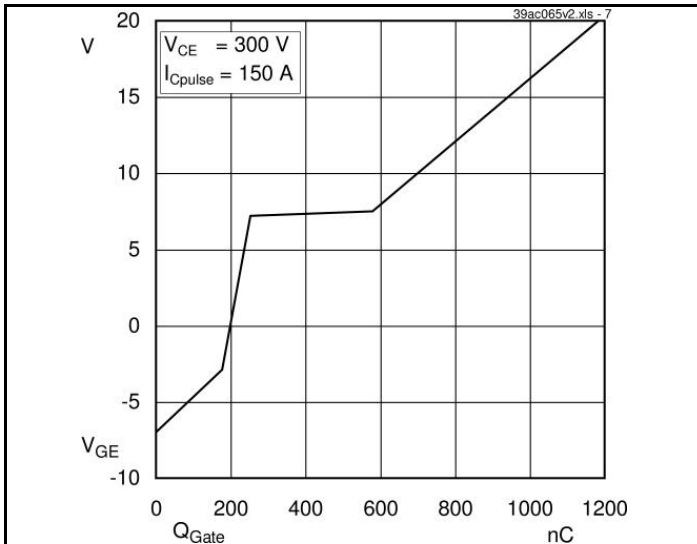


Fig. 7 Typ. gate charge characteristic

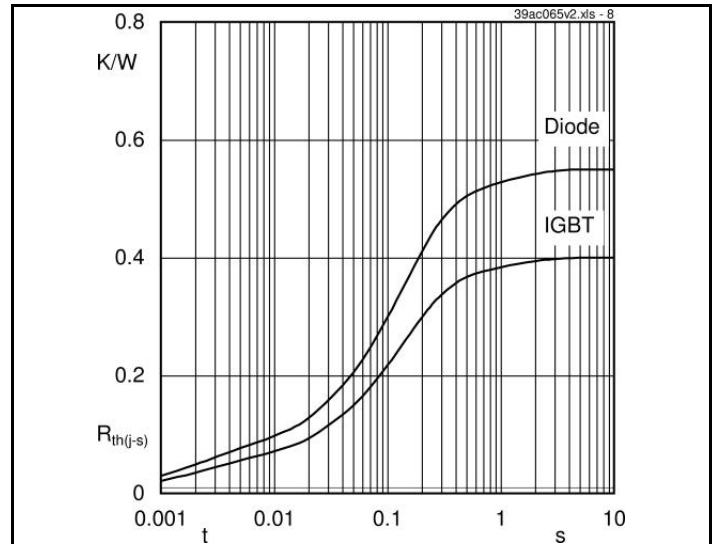


Fig. 8 Typ. thermal impedance

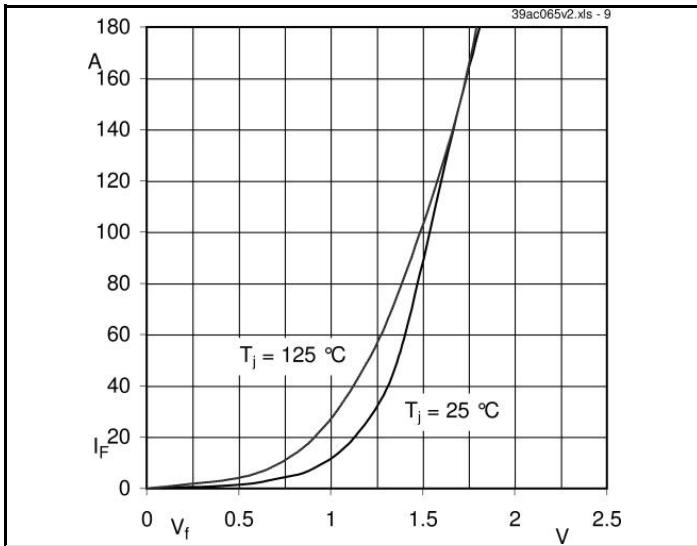
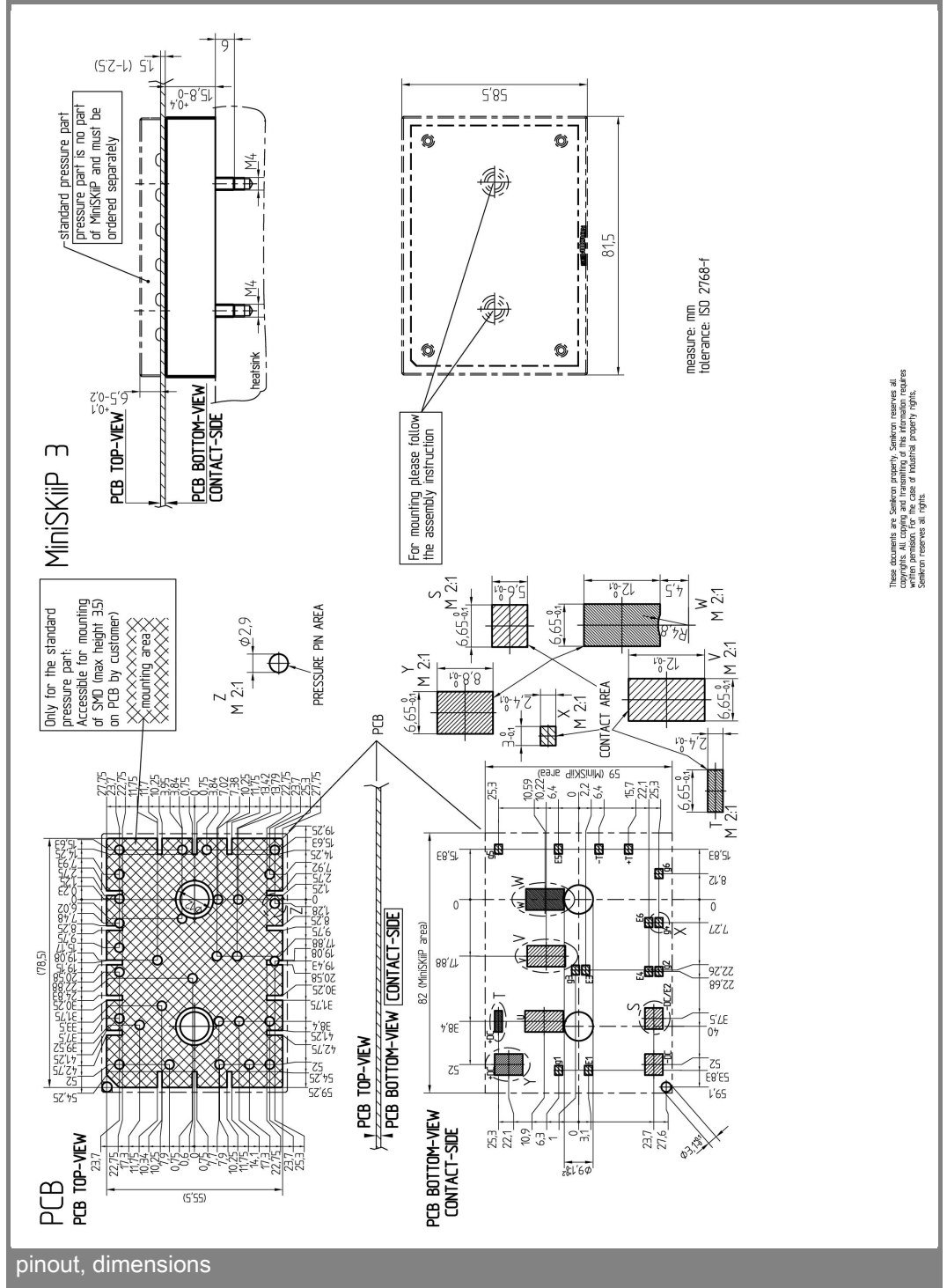
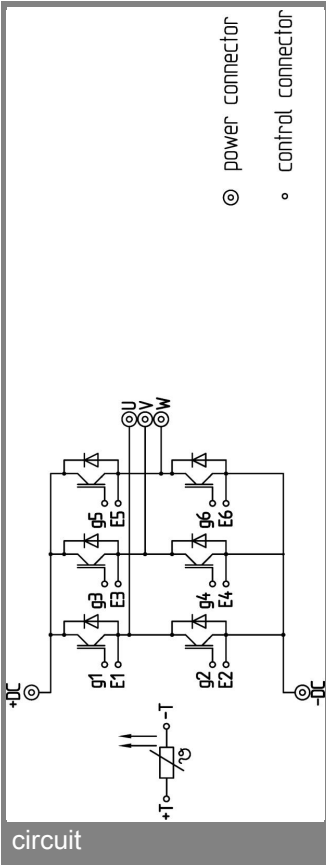


Fig. 9 Typ. freewheeling diode forward characteristic



These documents are Semikron property. Semikron reserves all
copyrights. All rights and transferring of this information requires
written permission of Semikron. All rights reserved.
Semikron reserves all rights.

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.